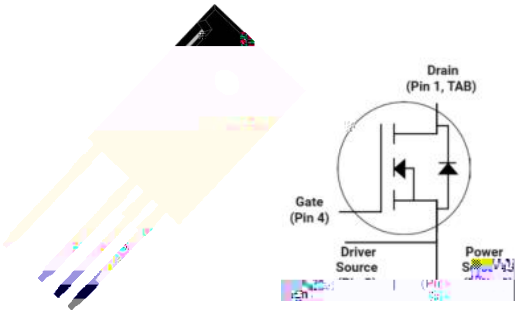
SG2M035120LJ

TriQSiC™ 1200V Silicon Carbide Power MOSFET G2

Features

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-
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Benefits

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-
-
-
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Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS}	$R_{DS(on),\ typ}$	$T_{J,max}$	Marking	Package

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1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note
				≤	

3 Electrical characteristics

3.1 Static characteristics

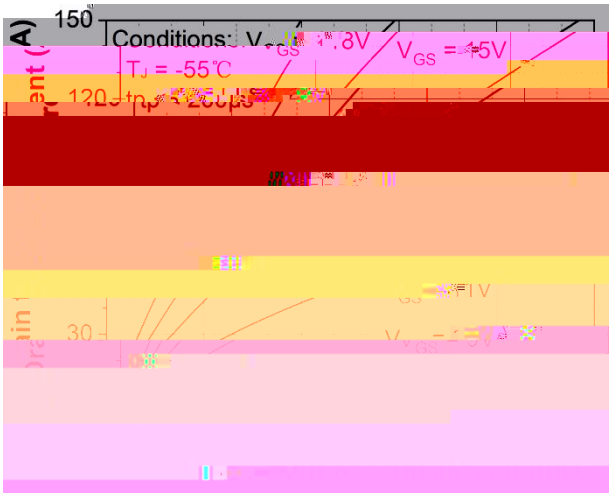
Table 4 Static characteristics

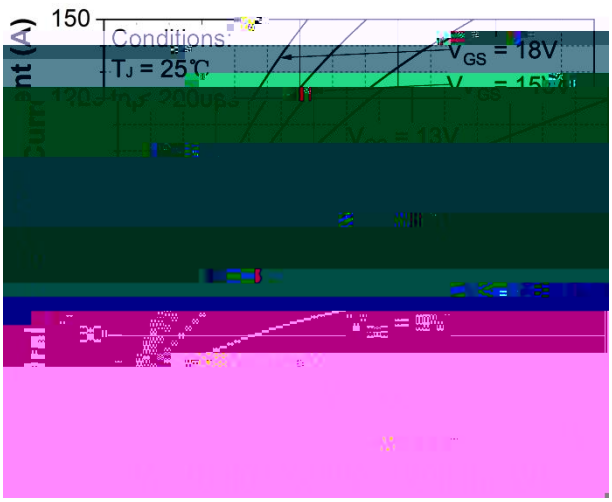
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
						•%C•	

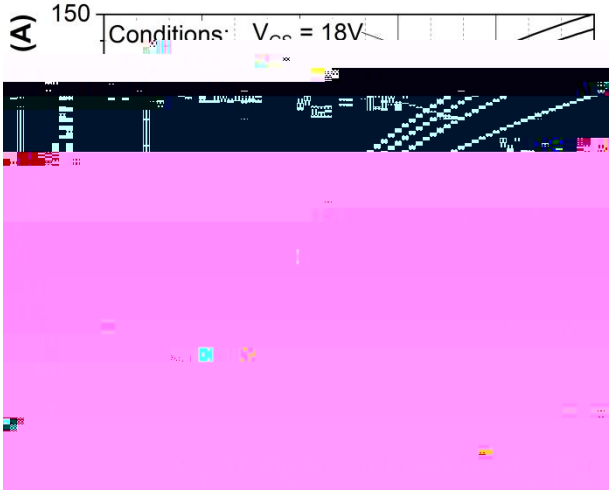
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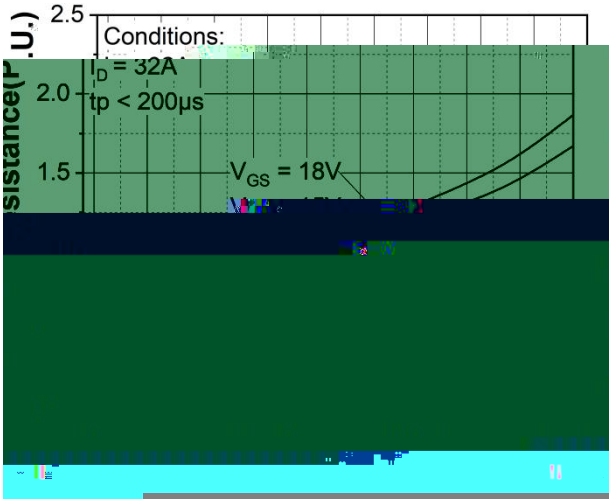
1200V SiC Power MOSFEo ȸr η6

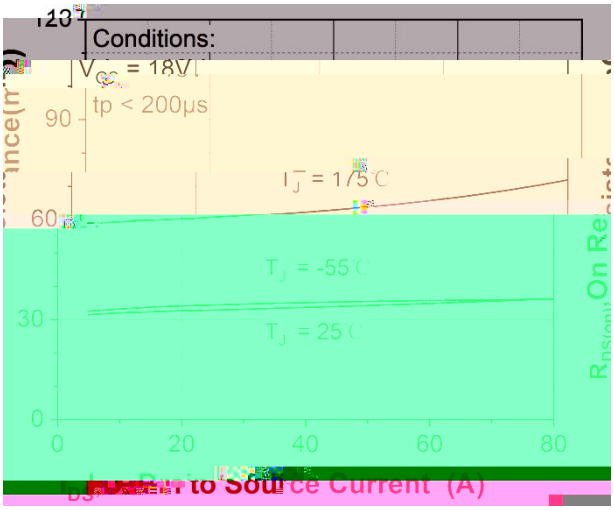
4 Electrical characteristic diagrams

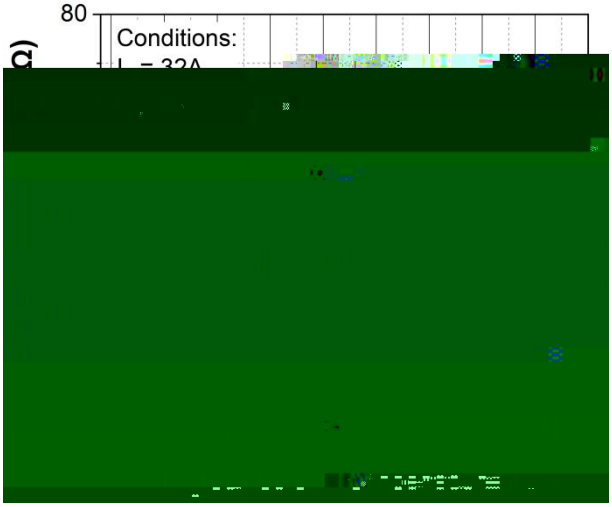




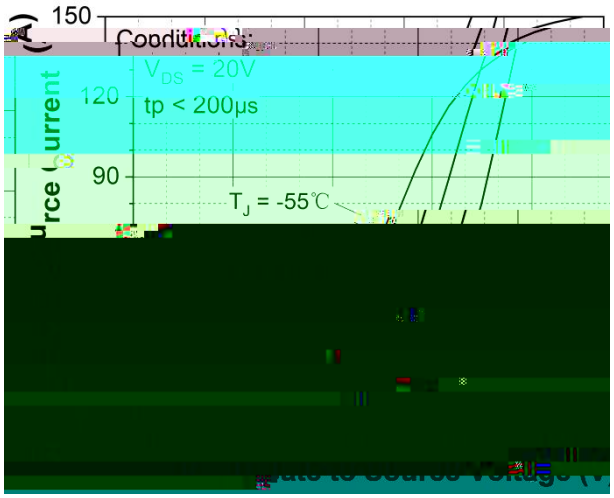


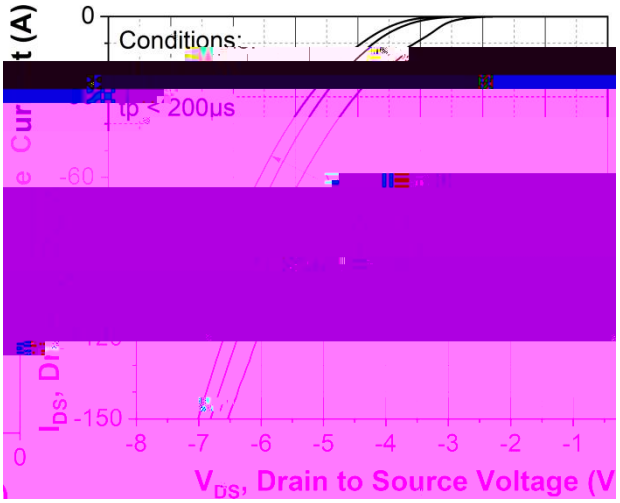


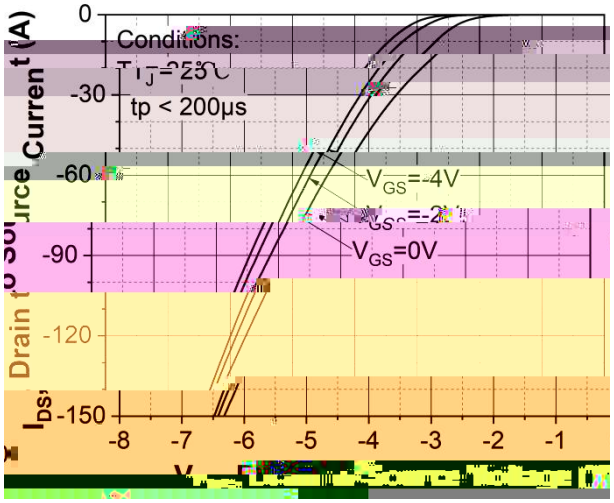


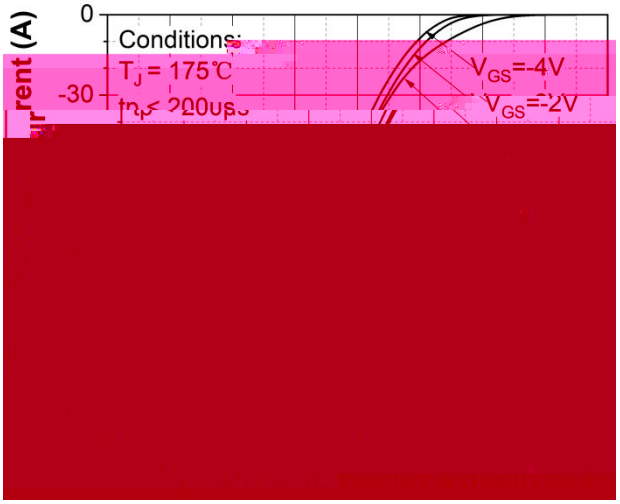


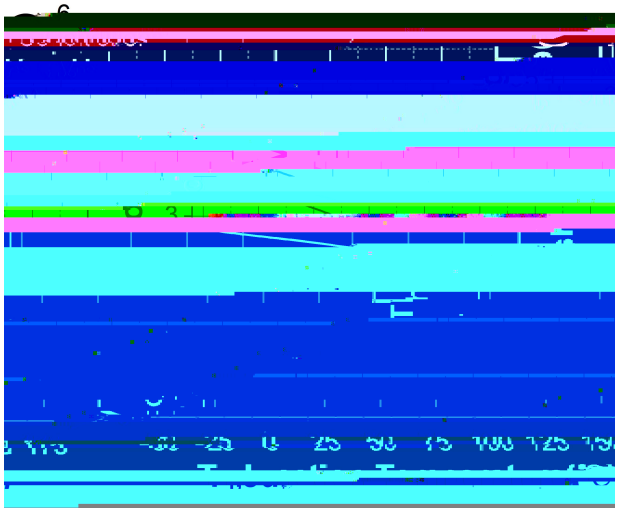
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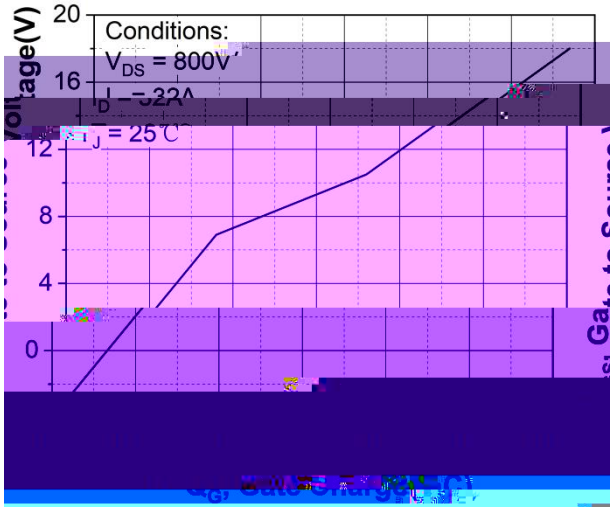




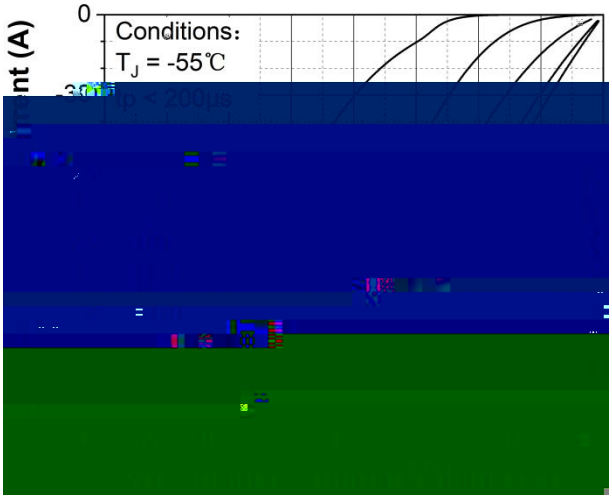


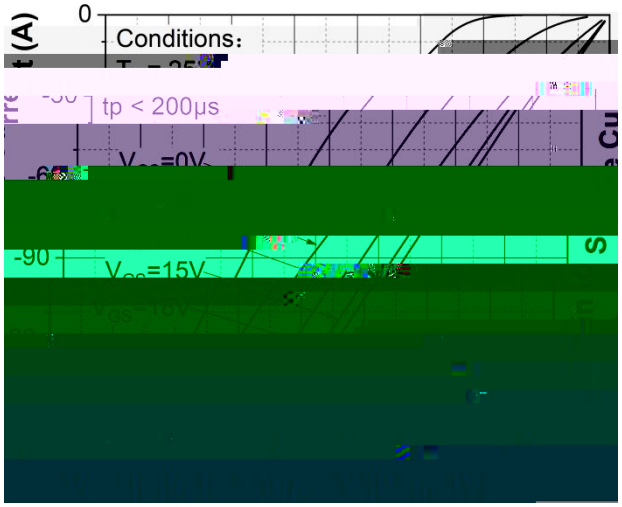


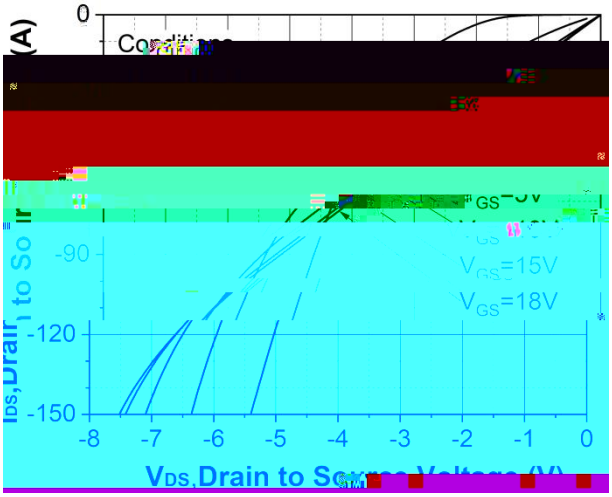


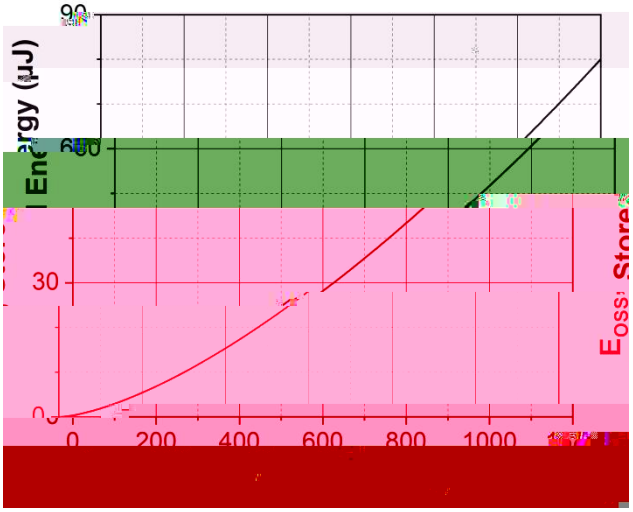


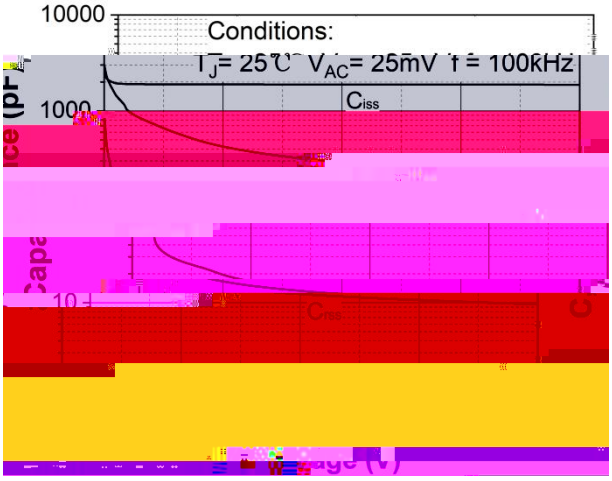
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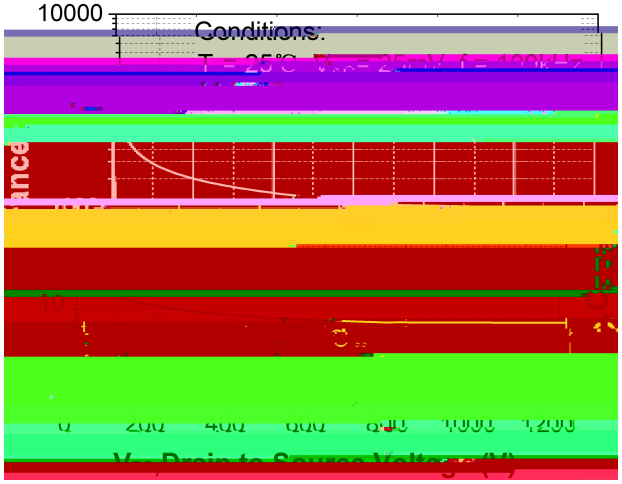






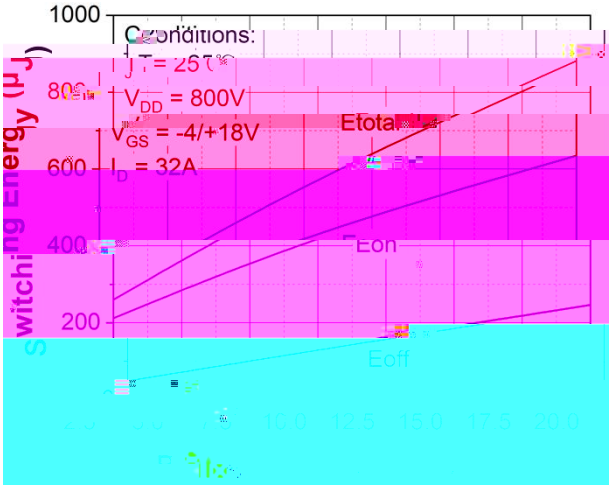


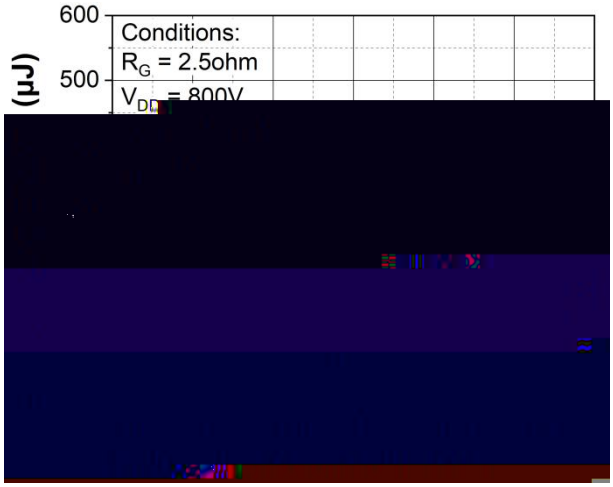


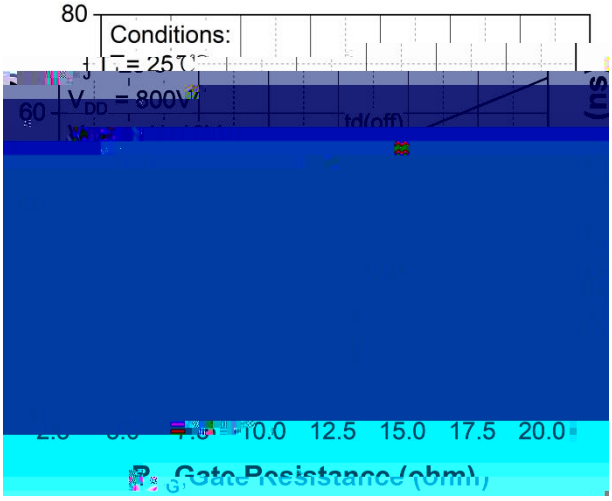


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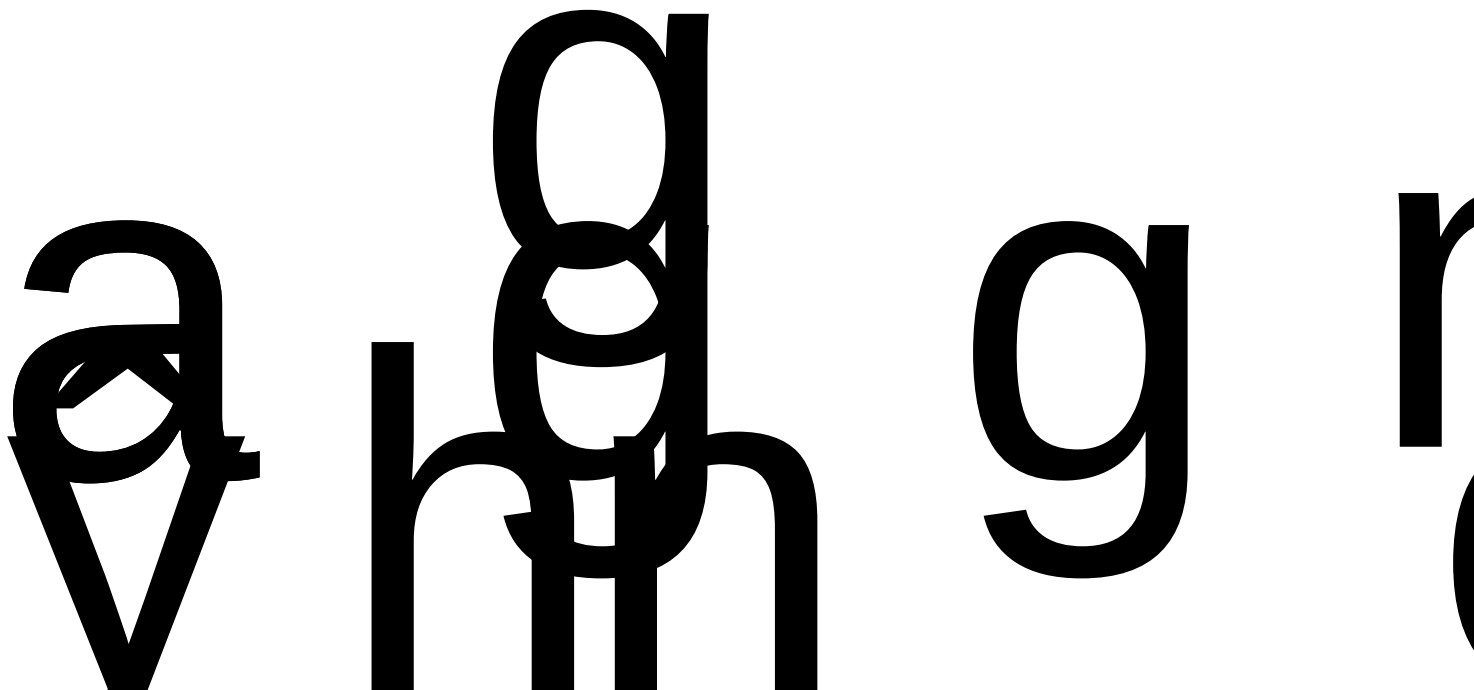




5 Package drawing

SG2M035120LJ

1200V SiC Power M



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1200V SiC Power MOSFET

Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2025-09-17	——	——
V01_01	2025-11-12	——	——
V01_02	2025-12-11	——	——
V01_03	2026-02-02	Final	——

Attention

RoHS compliance

REACH compliance

SG2M035120LJ